

Triple ALBO PCM Repeater

GENERAL DESCRIPTION

The XR-T5600/T5620 is a bipolar monolithic repeater IC designed for PCM carrier systems operating at 1.544 MBPS (T1), 2 MBPS, or 2.37 MBPS (T148C). it provides all of the active circuits required for one side of a PCM repeater.

FEATURES

Single 5.1V Power Supply Less than 10ns Sampling Pulse over the Operating Range Triple Matched ALBO Ports 2 MBPS Capability

APPLICATIONS

T1 PCM Repeater
T148C PCM Repeater
European 2 MBPS PCM Repeater
T1C PCM Repeater (requires external preamplifier)

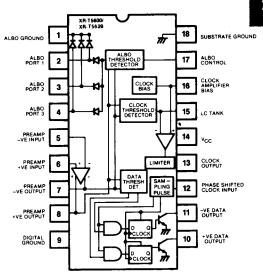
ABSOLUTE MAXIMUM RATINGS

Storage Temperature	-65°C to +150°C
Supply voltage	-0.5 to +10V
Supply Voltage Surge (10ms)	+25V
Input Voltage (except Pin 2, 3, 4, 17)	−0.5 to 7V
Input Voltage (Pin 2, 3, 4, 17)	-0.5 to +0.5V
Data Output Voltage (Pin 10, 11)	20V
Voltage Surge (Pin 5, 6, 10, 11) (10 m	nsec only) 50V

ORDERING INFORMATION

Part Number	Package	Operating Temperature
XR-T5600	Plastic	-40°C to 85°C
XR-T5620	Plastic or Ce	ramic -40°C to 85°C

PIN ASSIGNMENT



SYSTEM DESCRIPTION

The XR-T5600/T5620 performs most of the functions required for one side of a PCM repeater operating at 2 Mbit/s or similar baud rate. The integrated circuit amplifies the received positive and negative pulses and feeds them into Automatic Line Build Out (ALBO), clock and data threshold detectors, see Figure 1. The ALBO threshold detector ensures that the received pulses at Pins 7 and 8 have the correct amplitude and shape. This is carried out by controlling the gain and frequency shaping of the ALBO network with three variable impedance ALBO ports.

The clock threshold detector extracts timing information from the pulses received at Pins 7 and 8 and passes it into the external tank coil at Pin 15. The sinusoidal-type waveform is amplified into a square wave at Pin 13, and forwarded through an external phase shift network into Pin 12. This waveform provides the data sampling pulse which opens latches into which the data from the data threshold detectors is passed. The resulting pulses are stored for half a bit period (normally 488ns) in the latches. They appear as half-width output pulses at Pins 10 and 11.

XR-T5600/T5620

ELECTRICAL CHARACTERISTICS

Test Conditions: $T_A = 25^{\circ}C$, $V_{CC} = 5.1V \pm 5\%$, unless specified otherwise (see Figure 1).

PARAMETERS	PINS	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Supply Current	14		22	30	mA	
Data Output Leakage Current	10, 11	Ì	0	100	μA	$V_{pull-up} = 15V, V_{CC} = 5.35V$
ALBO Port Off Voltage	2, 3, 4		0	0.1	٧	
Amplifier Pin Voltage	5, 6, 7, 8	2.4	2.9	3.4	٧	
Dynamic Characteristics Amplific	or					
Output Offset Voltage		-50	0	50	mV	$R_S = 8.2k\Omega$
AC Gain @ 1MHz		47	50	53	₫B	
Input Impedance		20			kΩ	
Output Impedance				200	Ω	
ALBO				•		
ALBO Off Impedance		20		25	kΩ	
ALBO On Impedance				25	Ω	•
Thresholds						
ALBO Threshold		1.4	1.5	1.6	V	
Clock Threshold as % of ALBO Thr	eshold	68		80	%	
DATA Threshold as % of ALBO The	reshold	42		49	%	
Clock Drive Current		0.7		1.4	mA	At V _O = V _{ALBO} Threshold
Output Stages						$R_L = 130\Omega$, $V_{pull-up} = 5.1 \pm 5\%$
Output Pulse Rise Time				40	ns	
Output Pulse Fall Time				40	ns	
Output Pulse Width		224	244	264	ns	
Output Pulse Width Differential		-10		+10	ns	
Buffer Gate Voltage (Low)		0.65		0.95	V	
Buffer Gate Voltage Differential		-0.15		0.15	l v	

ELECTRICAL CHARACTERISTICS

Test Conditions: Unless otherwise stated, all characteristics shall apply over the operating temperature range of -40° C to $+85^{\circ}$ C with $V_{CC} = 5.1 \text{V} \pm 5\%$, all voltages referred to ground = 0V.

SYMBOL	PARAMETERS	PINS	MIN	TYP	MAX	UNIT	CONDITIONS
General (i	Ref. Figure 2)						
Is I _{LD}	Supply Current Data Output Leakage Current Amplifier Pin Voltages ALBO Ports Off Voltage	14 10, 11 5, 6, 7, 8 2, 3, 4	2.4	22 6 2.9 0	30 100 3.4 0.1	mΑ μΑ ∨ ∨	From V _S (See Note 1)

Note: 1) $V_S=15V$, $V_{CC}=5.35V$

Amplifier (Ref. Figure 2, Only Pins 1, 9, 10	18 connect	ed)				
Input Offset Voltage	5&6	-10		+10	m V	R _S = 8.2kΩ (See Note 1)
Input Bias Current	5 & 6	0		5	μΑ	R _S = 8.2kΩ (See Note 1)
Input Offset Current	5 & 6	-1		1	μΑ	R _S = 8.2kΩ (See Note 1)
Output Offset Voltage	7 & 8	-50	0	50	mV	R _S = 8.2kΩ (See Note 1)
Common Mode Rejection Ratio	7 & 8	30			dB	V _{CC} ± 10%
Output Voltage Swing	788	2.2			V	

Note: 1) R_S = Source Resistance

Clock Amplifier (Ref. Figure 2, Disc	onnect Pin 15 from Pin	16)			
Input Offset Voltage	15 & 16	0.5	6	mV	R _S = 10kΩ (See Note 1)
Input Bias Current	15 & 16		10	μА	T = 25°C (See Note 2)
Max. Output Voltage	13	0.7		·v	(See Note 3)
Min. Output Voltage	13	0.7		٧	(See Note 4
Max./Min. Output Voltage	Difference —	0.7	50	mV	(See Note 5)

Notes:

- 1. R_S = Source resistance, Pin 15 positive with respect to Pin 16
- 2. Pin 15 = Pin 16 = 3.6V
- 3. Pin 15 = 2.6V, Pin 16 = 3.6V
- 4. Pin 15 = 4.6V, Pin 16 = 3.6V
- 5. Calculation only

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SYMBOL	PARAMETERS	PINS	MIN	TYP	MAX	UNIT	CONDITIONS
LBO (Re	f. Figure 2)						
	On Current	1	3			mA	$V_8 - V_7 = \pm 1.75V$
	Drive Current	17	0.4		1.4	mA	$V_8 - V_7 = \pm 1.75V$
	Resistance Pin 17 to Ground		35	50	70	kΩ	Not Powered

DYNAMIC CHARACTERISTICS

Amplifier (Ref. Figure 3)						
Ao AC Gain @ 1MHz Zin Input Impedance Zout Output Impedance	5 to 8 5 7, 8	47 20	50	53 200	dB kΩ Ω	(See Note 1) (See Note 2)

Notes:

1) At 1 MHz, AC ground Pins 7 and 8, disconnect 51Ω resistor, allow for in-circuit R, C

2) At 1MHz, use Figure 2

lock An	nplifier (Ref. Figure 3)					
A _o BW t _d Z _{out}	AC Gain -3dB Bandwidth Delay Output Impedance	15,16 to 13 15,16 to 13 15 to 13 13	32 10 8	12 200	dB MHz ns Ω	(See Note 1 (See Note 2) (See Note 3) (See Note 4)

Notes:

- 1) Remove dc offset, at 2.048MHz, Pin 13 = 1Vpk-pk sine wave
- 2) Remove dc offset, Pin 13 = 1Vpk-pk sine wave
- 3) Remove dc offset, Pin 15 = 2Vpk-pk sine wave; delay from Pin 15 negative-going zero crossover to Pin 13 positive edge
- 4) Remove dc offset, at 2.048MHz

LBO (Ref. Figure 2)					
Off Impedance	2,3,4	20		kΩ	(See Note 1)
Intermediate Impedance Difference	2,3,4		5	%	(See Note 2)
On Impedance	2,3,4		25	Ω	(See Note 3)
Transconductance	7/8 to 1		0.03	dB	(See Note 4)

Notes:

- 1) At 1MHz, allow for in-circuit R, C
- 2) At 1MHz, V₈-V₇ adjusted for current at Pin 1 = 100μA
- 3) At 1MHz, V₈-V₇ adjusted for ±1.75V
- 4) At 1MHz, change in V_8-V_7 for current at Pin 1 = 10 μ A to 100 μ A

SYMBOL	PARAMETERS	PINS	MIN	TYP	MAX	UNIT	CONDITIONS
Threshold	Voltages (Ref. Figure 3)						
	ALBO Threshold +ve	8-7	1.4	1.5	1.6	V	(See Notes 1 & 2)
	ALBO Threshold -ve	7-8	1.4	1.5	1.6	V	(See Notes 1 & 2)
	ALBO Threshold Difference	_	-5	o	5	%	(See Note 3)
	Clock Drive on Current (peak) +ve	18		1.0	1.4	mA	(See Note 4)
	Clock Drive on Current (peak) -ve	18		1.0	1.3	mA	(See Note 5)
	Clock Drive on Current Difference	_	-5	0	5	%	(See Note 3)
	Clock Threshold +ve	87	68		80	%	(See Notes 1, 6, 8)
	Clock Thresholdve	7-8	68		80	%	(See Notes 1, 7, 8)
	Clock Threshold Difference	_	-5	0	5	%	(See Note 3)
	Data Threshold +ve	8-7	44	46	48	%	(See Notes 1, 8, 9, 11
	Data Threshold -ve	7-8	44	46	48	%	(See Notes 1, 8, 10, 1
	Data Threshold Difference	_	-3	0	3	%	(See Note 3)

Notes:

- Pk/pk voltage at Pins 7 and 8 of a 1MHz sine wave derived through amplifier and measured differentially
- 2) Pk/pk voltage at Pins 7 and 8 adjusted for current at Pin 1 = 3mA
- 3) Calculation only percentage difference calculated from $\left(\frac{\text{higher value}}{\text{lower value}} 1\right) \times 100\%$
- V₈-V₇ adjusted to ALBO threshold +ve voltage, ref. Pin 16 = 3.6V
- 5) V_7 - V_8 adjusted to ALBO threshold -ve voltage, ref. Pin 16 = 3.6V
- 6) V_8-V_7 adjusted to peak current at Pin 18 = 1/2 (clock drive on current peak +ve)
- 7) $V_7 V_8$ adjusted to peak current at Pin 18 = 1/2 (clock drive on current peak -ve)
- 8) Figure taken as a percentage of lower ALBO threshold
- 9) V₈-V₇ increased until 1MHz PRF on counter at Pin 10
- 10) V7-V8 increased until 1MHz PRF on counter at Pin 11
- 11) With 2,048MHz 2Vpk-pk sine wave to Pin 15 with 180 μ H parallel with 36 Ω to Pin 16 = 3.6V

t _r	Output Pulse Rise Time +ve	10			40	ns	10%-90%
t,	Output Pulse Rise Time -ve	11			40	ns	10%-90%
t _i	Output Pulse Fall Time +ve	10			40	ns	10%-90%
t _f	Output Pulse Fall Time -ve	11			40	ns	10%-90%
t _w	Output Pulse Width +ve	10	224	244	264	ns	at 50%
	Output Pulse Width -ve	11	224	244	264	ns	at 50%
∆t _w	Output Pulse Width Difference	_	-10		10	ns	
VoL	Buffer Gate Voltage (low) +ve	10	0.65		0.95	٧	
VoL	Buffer Gate Voltage (low) -ve	11	0.65		0.95	٧	
ΔVOL	Buffer Gate Voltage Difference		-0.15		0.15	V	

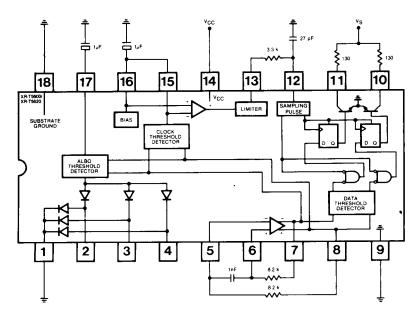


Figure 2. D.C. Parameter Test Circuit

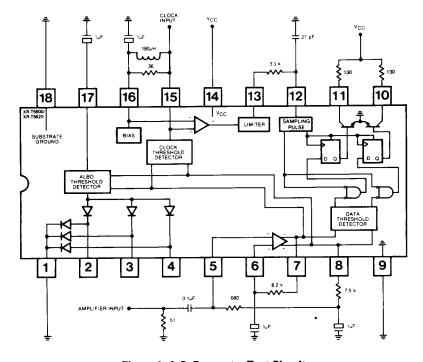


Figure 3. A.C. Parameter Test Circuit

SYMBOL PARAMETERS PINS MIN TYP MAX UNIT CONDITIONS							CONDITIONS		
Sample Pulse Width (Ref. Figure 4, C _Y = 27pF)									
Sar	nple Pulse width			10		ns	(See Notes 1 5)		

Notes:

- 1) The sample pulse width is the period during which the output latches are opened to accept a signal above the data hold at Pin 7 or 8 and cause a half-width output pulse at Pin 11 or 10 respectively.
- 2) Sample pulse width is specified with a 2.048MHz TTL waveform at clock input (Pin 15) and a 2,400MHz Schottky TTL waveform at amplifier input in the circuit of Figure 4. Figure 7 shows the relevant IC waveforms.
- Monitor the frequency of coincident output pulses at Pins 10 and 11 either directly or through output circuit to frequency counter.
- 4) Sample pulse width = X ns + (0,1 x measured frequency in kHz) ns where X is the mean rise/fail times of the waveform at Pin 8 between 25% and 75%.
- 5) X to be within the range of 10nx < X < 12ns. THis requires HF layout techniques with the amplifier operated closed loop.

	Sample Pulse Generator Input Waveform (Pin 12 — Ref. Figure 4, C _Y = 40pF)										
Output Pulse Frequency 10, 11 1.024 1.024 1.024 MHz (See Note 1)		Output Pulse Frequency	10, 11	1.024	1.024	1.024	MHz	(See Note 1)			

Note:

1) With 2.048MHz ± 100ppm TTL waveform at clock input. With half of above waveform frequency at amplifier input.

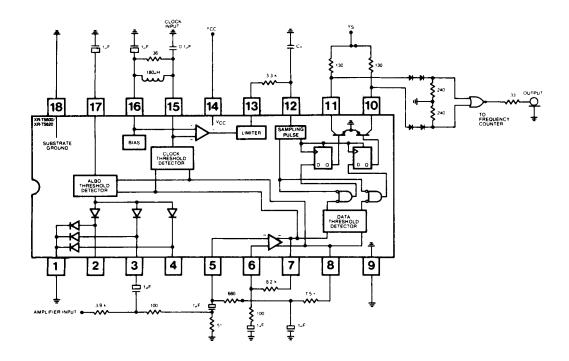


Figure 4. Sampling Pulse Test Circuit

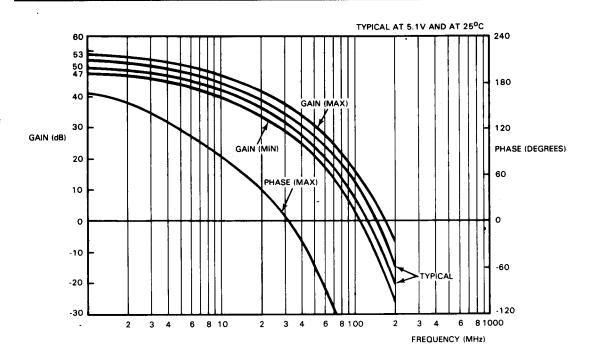


Figure 5. Typical and Limiting Values of Gain and Phase

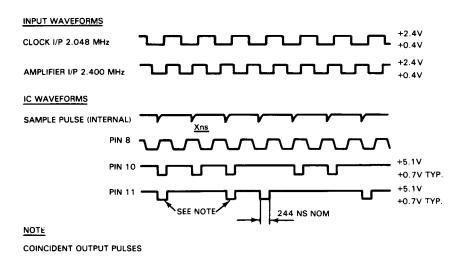


Figure 6. IC Waveforms for Measuring Sampling Pulse Width

